



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Confirmation No.: 4555

SHIBATA et al.

Group Art Unit: 2826

Appln. No.: 09/985,927

Examiner: A. SEFER

Filed: November 6, 2001

Title: GROUP III NITRIDE COMPOUND SEMICONDUCTOR DEVICE AND METHOD FOR PRODUCING THE SAME

#5/B

9/19/02  
Shm th

September 13, 2002

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AMENDMENT UNDER 37 C.F.R. § 1.111

Hon. Commissioner of Patents  
Washington, D.C. 20231

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SEP 17 2002  
TECHNOLOGY CENTER 2800

Sir:

In reply to the Office Action dated June 14, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please enter amended claim 5 as follows:

5. (Amended) A group III nitride compound semiconductor device comprising:  
a substrate on which a first environment division and a second environment division are formed; and  
group III nitride compound semiconductor layers formed on said first environment division so as to serve as effective semiconductor layers, wherein the group III nitride compound semiconductor device is produced by a method comprising, in order:  
forming the second environment division on a surface of a substrate;  
forming a mask on a surface of a first portion of the second environment division;  
removing a second portion of the second environment division on which the mask is not formed to thereby form the first environment division in an area in which the mask is not formed;  
removing the mask; and laminating a plurality group III nitride compound semiconductor layers for constituting a device on said first environment division.

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